Received: 2-4-2004

~~ ~~	Rec	ervea		PTO/SB/08A (04-03)					
Substitute fo	or form 1449A/PTO	·		Complete if Known					
				Application Number	10/771,855				
	INFORMATIO	N DISCLOSU	IRE	Filing Dale	February 4, 2004				
	STATEMENT	RY APPLICA	NT	First Named Inventor	Marius K. Orlowski et al.				
ļ	SIATEMENT	DI AITEIOA		Group Art Unit	2813				
(use as man)	y sheets as necessar	n		Examiner Name					
Sheet	1	of	1	Attorney Docket Number	SC13155TP				

U. S. PATENT DOCUMENTS									
Examiner Initials*	Cite No. 1	Document Number Number -Kind Code? (if known)	Publication Date MM-DD-YYYY	Nam	e of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Ro Passages or Relevant Figures A			
&WX		US 2002/0135020 A1	09-26-2002	Skotn	icki et al.				
11.2	AB	US -2002/0097608 A1	07-25-2002	Skotn	icki et al.				
RUNG	, AC	US6,369,438 B1	04-09-2002	Sugiy	ama et al.				
		US-							
		US-							
		US-							
		US-							
		US-							
		US-							
		US-							
	I	US-							
		FC	REIGN PATENT DO	CUMENT	S	······			
Examine r	xamine Cite No. 1 Foreign Patent Document Country Code ³ Number 4 Kind Code ² (if				Name of Patentee or Applicant of Cited Documen	Pages, Columns, Lines, Where Relevant Passages or	7 6		

FOREIGN PATENT DOCUMENTS										
Examine	Cite No. 1	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or	Pages, Columns, Lines,	7 6				
r	}	Country Code ³ Number ⁴ Kind Code ² (if		Applicant of Cited Document	Where Relevant Passages or	İ				
Initials*	1	known)			Relevant Figures Appear					
	1	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \			و					
						/				
	·	1			<u> </u>					

		NON PATENT LITERATURE DOCUMENTS						
Examiner Initials	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.						
2.W.S.	AD	MONFRAY, S. et al.; "First 80nm SON (Silicon-On-Nothing) MOSFETs with perfect morphology and high electrical performance"; IEEE; 2001; pp 29.7.1 - 29.7.4.						
I.N.Z.	AE	JURCZAK, MALGORZATA et al.; "Silicon-on-Nothing (SON)—an Innovative Process for Advanced CMOS"; IEEE Transactions on Electron Devices,; November 2000; Vol. 47; No. 11, pp. 2179—2187.						
		4 0						

Examiner Signature	X	eh	Ren	\mathcal{T}	,	mos		Date Considered	Seo.	tember	- 3	200
EXAMINER: Initial if relation to a	reno	e considere	ed, whether or n	ot citation	is in conform	nance with MPEP 609.	Oraw line th	rough citation, if not in	n conformance a	and not considered. Incl	ude copy of t	his form with

¹ Unique clation dasignation number. ² Applicant is to place a check mark here if English Language Translation is attached.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.